

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

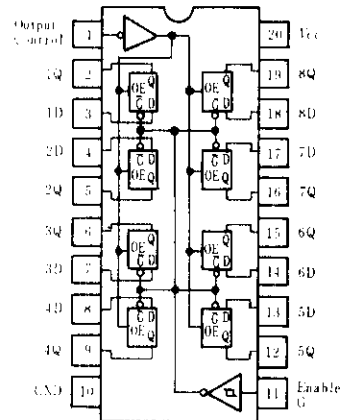
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# HD74LS373 Octal D-type Transparent Latches (with three-state outputs)

The HD74LS373, 8-bit register features totem-pole three-state outputs designed specifically for driving highly-capacitive or relatively low-impedance loads. The high-impedance third state and increased high-logic-level drive provide this register with the capacity of being connected directly to and driving the bus lines in a bus-organized system without need for interface or pull-up components. They are particularly attractive for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The eight latches are transparent D-type latches meaning that while the enable (G) is high the Q outputs will follow the data (D) inputs. When the enable is taken low the output will be latched at the level of the data that was setup.

## PIN ARRANGEMENT



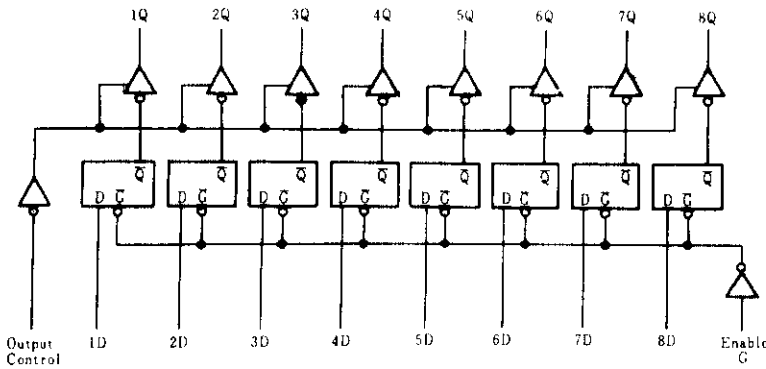
(Top View)

## FUNCTION TABLE

Inputs			Output
Output control	Enable G	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q <sub>0</sub>
H	X	X	Z

Notes: H = high level, L = low level,  
X = irrelevant  
Q<sub>0</sub> = level of Q before the indicated steady-state input conditions were established.  
Z = off (high-impedance) state of a three-state output

## BLOCK DIAGRAM



## RECOMMENDED OPERATING CONDITIONS

Item	Symbol	min	typ	max	Unit
Supply voltage	V <sub>CC</sub>	4.75	5.00	5.25	V
Output voltage	V <sub>OH</sub>	—	—	5.5	V
Output current	I <sub>OH</sub>	—	—	-2.6	mA
	I <sub>OL</sub>	—	—	24	mA
Enable pulse width	t <sub>w</sub>	"H" level	15	—	ns
		"L" level	15	—	ns
Data setup time	t <sub>su</sub>	5 ↓	—	—	ns
Data hold time	t <sub>h</sub>	25 ↓	—	—	ns

Note) ↓ : The arrow indicates the falling edge of clock pulse.

## ■ ELECTRICAL CHARACTERISTICS ( $T_a = -20 \sim +75^\circ\text{C}$ )

Item	Symbol	Test Conditions	min	typ*	max	Unit	
Input voltage	$V_{IH}$		2.0	—	—	V	
	$V_{IL}$	Data inputs	—	—	0.7	V	
G, Output control inputs		—	—	0.8	V		
Output voltage	$V_{OH}$	$V_{CC} = 4.75\text{V}$ , $V_{IH} = 2\text{V}$ , $V_{IL} = V_{IL\text{max}}$ , $I_{OH} = -2.6\text{mA}$	2.4	—	—	V	
	$V_{OL}$	$V_{CC} = 4.75\text{V}$ , $V_{IH} = 2\text{V}$ , $V_{IL} = V_{IL\text{max}}$	$I_{OL} = 12\text{mA}$	—	—	0.4	V
$I_{OL} = 24\text{mA}$			—	—	0.5	V	
Off-state output current	$I_{OZH}$	$V_{CC} = 5.25\text{V}$ , $V_{IH} = 2\text{V}$	$V_O = 2.7\text{V}$	—	—	20	$\mu\text{A}$
	$I_{OZL}$		$V_O = 0.4\text{V}$	—	—	-20	$\mu\text{A}$
Input current	$I_{IH}$	$V_{CC} = 5.25\text{V}$ , $V_I = 2.7\text{V}$	—	—	20	$\mu\text{A}$	
	$I_{IL}$	$V_{CC} = 5.25\text{V}$ , $V_I = 0.4\text{V}$	—	—	-0.4	$\text{mA}$	
	$I_I$	$V_{CC} = 5.25\text{V}$ , $V_I = 7\text{V}$	—	—	0.1	$\text{mA}$	
Short-circuit output current	$I_{OS}$	$V_{CC} = 5.25\text{V}$	-30	—	-130	$\text{mA}$	
Supply current	$I_{CC}$	$V_{CC} = 5.25\text{V}$ , $V_I = 4.5\text{V}$ (Output control)	—	24	40	$\text{mA}$	
Input clamp voltage	$V_{IK}$	$V_{CC} = 4.75\text{V}$ , $I_{IN} = -18\text{mA}$	—	—	-1.5	V	

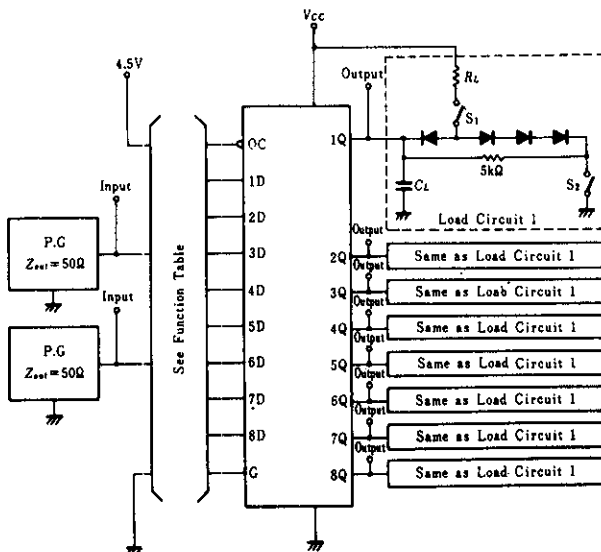
\*  $V_{CC} = 5\text{V}$ ,  $T_a = 25^\circ\text{C}$

## ■ SWITCHING CHARACTERISTICS ( $V_{CC} = 5\text{V}$ , $T_a = 25^\circ\text{C}$ )

Item	Symbol	Input	Output	Test Conditions	min	typ	max	Unit
Propagation delay time	$t_{PLH}$	D	Q	$C_L = 45\text{pF}$ $R_L = 667\Omega$	—	12	18	ns
	$t_{PHL}$				—	12	18	
	$t_{PLH}$	G	Q		—	20	30	
	$t_{PHL}$				—	18	30	
Output enable time	$t_{ZH}$	OC	Q		—	15	28	
	$t_{ZL}$				—	25	36	
Output disable time	$t_{HZ}$	OC	Q	$C_L = 5\text{pF}$ $R_L = 667\Omega$	—	12	20	
	$t_{LZ}$				—	15	25	

## ■ TESTING METHOD

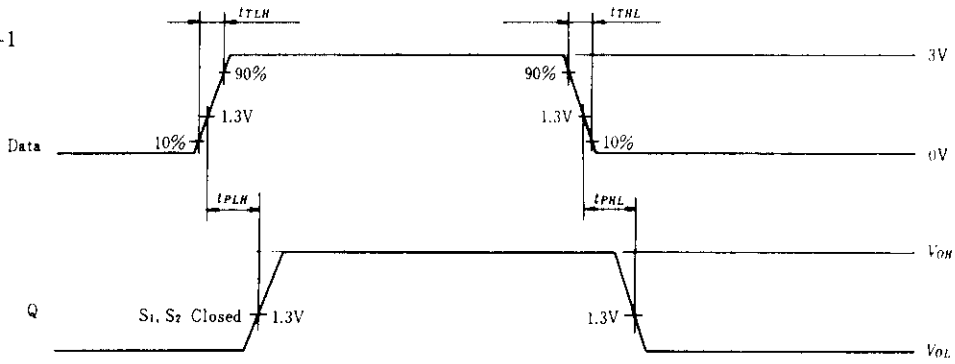
Test Circuit



- Notes:
1.  $C_L$  includes probe jig capacitance.
  2. All diodes are 1S2074 (H).

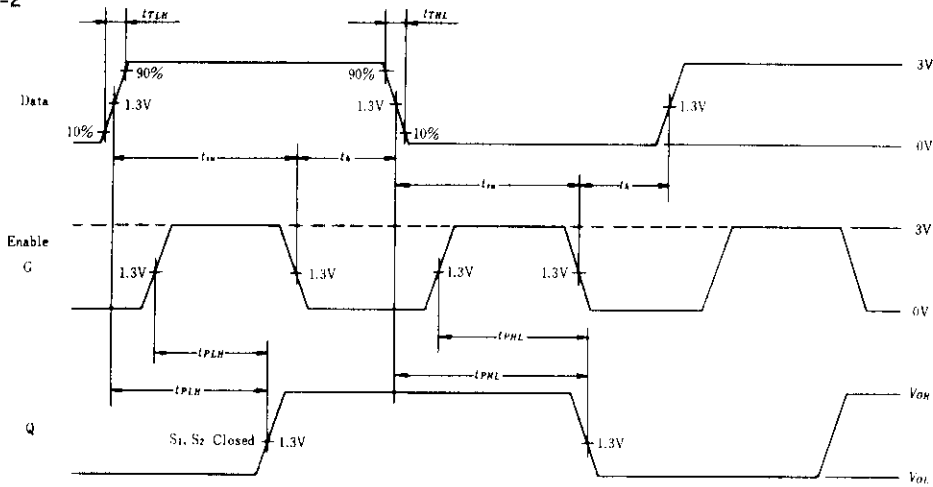
# HD74LS373

Waveform-1



Notes: Input pulse;  $t_{TLH} \leq 15\text{ns}$ ,  $t_{THL} \leq 6\text{ns}$ ,  $PRR = 1\text{MHz}$ , duty cycle 50%

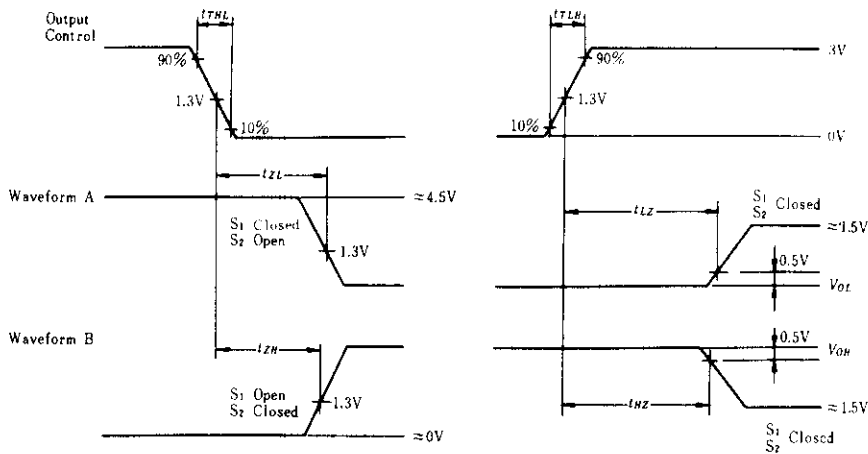
Waveform-2



Note: Enable input pulse;  $t_{TLH} \leq 15\text{ns}$ ,  $t_{THL} \leq 6\text{ns}$ ,  $PRR = 1\text{MHz}$

Data input pulse;  $t_{TLH} \leq 15\text{ns}$ ,  $t_{THL} \leq 6\text{ns}$ ,  $PRR = 1\text{MHz}$ , G input is high.

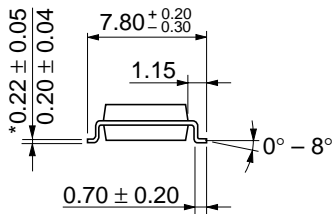
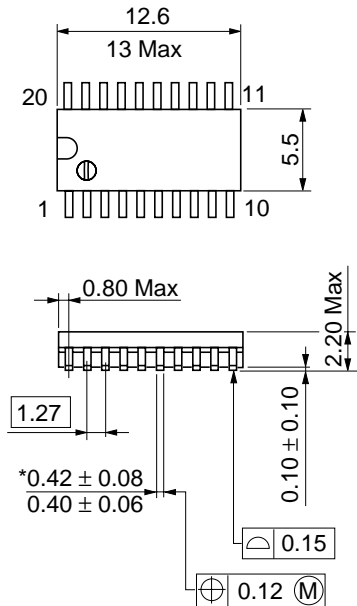
Waveform-3



Notes: 1. Input pulse;  $t_{TLH} \leq 15\text{ns}$ ,  $t_{THL} \leq 6\text{ns}$ ,  $PRR = 1\text{MHz}$ , duty cycle 50%  
2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.

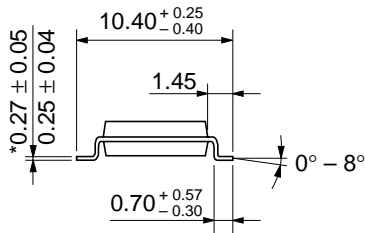
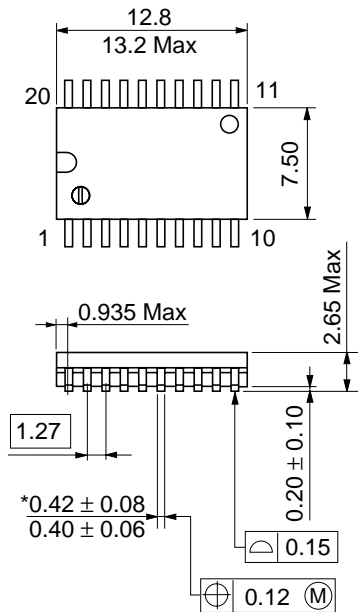


Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.26 g



Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.31 g

\*Dimension including the plating thickness  
Base material dimension



Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g

\*Dimension including the plating thickness  
 Base material dimension



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